



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on) max}	Ι _D T _A = +25°C
-30V	70mΩ@ V _{GS} = -10V	-3.8A
	120mΩ@ V _{GS} = -4.5V	-3.0A

Description and Applications

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

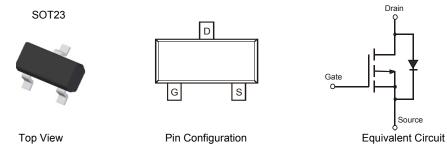
- Power Management Functions
- Analog Switch
- Load Switch
- Boost Switch

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208 3
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



Ordering Information (Note 5)

Case	Packaging
SOT23	3,000/Tape & Reel
	SOT23

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

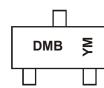
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q10x qualified and are PPAP capable. Automotive, AEC-Q10x and standard products are electrically and thermally

- the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



DMB = Product Type Marking Code YM = Date Code Marking Y = Year (ex: A = 2013) M = Month (ex: 9 = September)

Date Code Key

Notes:

Ballo boad hiley												
Year	2012		2013	2014		2015	2016		2017	2018		2019
Code	Z		А	В		С	D		E	F		G
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characterist	ic		Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage		V _{GSS}	±20	V	
Drain Current (Note 6) V _{GS} = -10V	Note 6) $V_{GS} = -10V$ Steady State $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$			-3.8 -2.9	А
Pulsed Drain Current (Note 7)		I _{DM}	-11	А	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 6)	PD	1.08	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 6)	$R_{ ext{ heta}JA}$	115	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

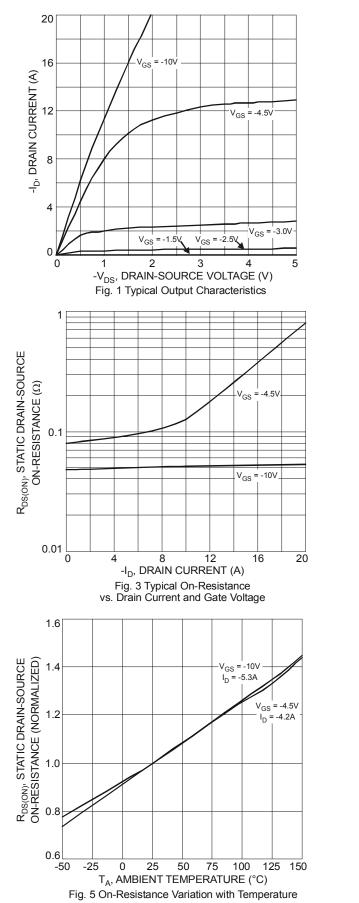
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)	-						
Drain-Source Breakdown Voltage	BV _{DSS}	-30		_	V	V _{GS} = 0V, I _D = -250µA	
Zero Gate Voltage Drain Current	I _{DSS}	_		-800	nA	V _{DS} = -30V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	V_{GS} = ±20V, V_{DS} = 0V	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(th)}	-1.0	-1.8	-2.1	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
Static Drain-Source On-Resistance	Р		56	70	mΩ	V _{GS} = -10V, I _D = -3.8A	
	R _{DS(ON)}	_	98	120	11122	V _{GS} = -4.5V, I _D = -3.0A	
Forward Transfer Admittance	Y _{fs}	_	3.6	—	S	V _{DS} = -5V, I _D = -2.7A	
Diode Forward Voltage (Note 7)	V _{SD}	_	_	-1.26	V	V _{GS} = 0V, I _S = -2.7A	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	—	336	1008	pF		
Output Capacitance	Coss	_	70	210	pF	V _{DS} = -25V, V _{GS} = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	49	147	pF		
Gate Resistance	R _G	_	4.6	—	Ω	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz	
SWITCHING CHARACTERISTICS (Note 9)							
Total Gate Charge	Qg	—	4.0	8.0		V _{DS} = -15V, V _{GS} = -4.5V, I _D = -3.8A	
		_	7.8	—	nC		
Gate-Source Charge	Q _{gs}	_	1.0	—		V _{DS} = -15V, V _{GS} = -10V, I _D = -3.8A	
Gate-Drain Charge	Q _{gd}	_	2.5	_			
Turn-On Delay Time	t _{d(on)}	_	6.0	12.0		V _{DS} = -15V, V _{GS} = -10V,	
Rise Time	tr	_	5.0	10.0			
Turn-Off Delay Time	t _{d(off)}	_	17.6	35.2	ns	$I_D = -1A, R_G = 6.0\Omega$	
Fall Time	t _f	_	9.5	19.0			

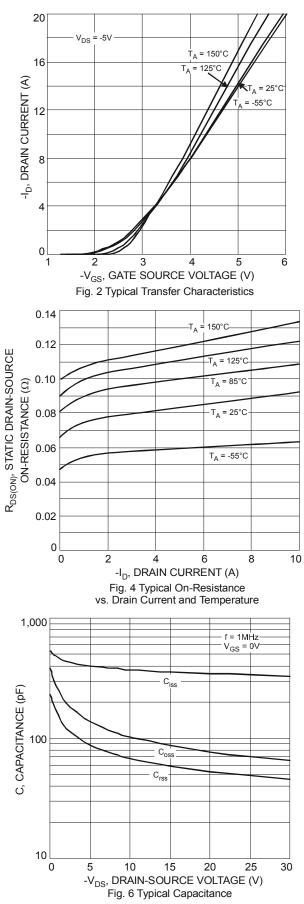
6. Device mounted on FR-4 PCB on 2 oz., 0.5 in.² copper pads and t ≤5 sec.
7. Pulse width ≤10µS, Duty Cycle ≤1%.
8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to production testing.

Notes:







1.2

1

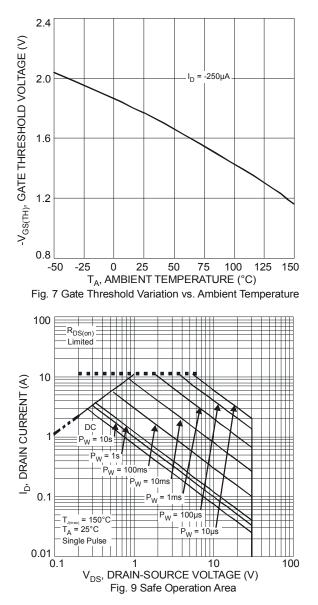
T_A = 25°C

0.8

-V_{SD}, SOURCE-DRAIN VOLTAGE (V)

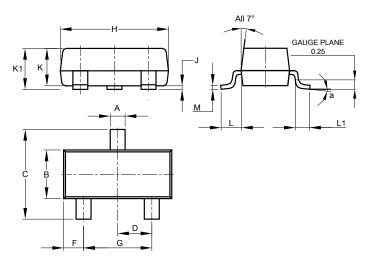
Fig. 8 Diode Forward Voltage vs. Current







Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
κ	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
α	8°						
All	All Dimensions in mm						

10

8

6

4

2

0

0.4

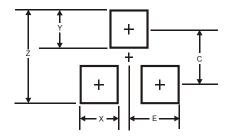
0.6

-I_S, SOURCE CURRENT (A)



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35

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